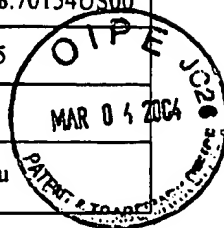


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INFORMATION DISCLOSURE STATEMENT BY APPLICANT		FILING DATE: August 22, 2001	CONFIRMATION NO.: 8935
		APPLICANT: Charles M. Lieber, et al.	
		GROUP ART UNIT: 2811	EXAMINER: Shouxiang Hu
Sheet	1	of	1



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*a copy of this reference is not provided as it was previously cited by or submitted to the office in a prior application, Serial No. __, filed __, and relied upon for an earlier filing date under 35 U.S.C. 120 (continuation, continuation-in-part, and divisional applications).

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Sheet	1	of	2

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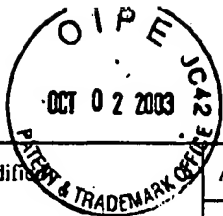
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Sheet	1	of	1

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SR		Office Action mailed 01/15/2003 in co-pending U.S. Patent Application No. 10/020,004, filed 12/11/2001		

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